

Band Switching Diode

- **Applications**

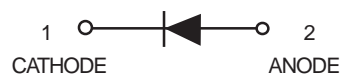
High frequency switching

- **Features**

- 1) Small surface mounting type.
- 2) High reliability.

- **Construction**

Silicon epitaxial planar



Device Marking

LBA277AT1 = 1

Absolute maximum ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	35	V
DC forward current	I _F	100	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+125	°C

Electrical characteristics (T_A=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	–	–	1.0	V	I _F =10mA
Capacitance between terminals	I _R	–	–	10	nA	V _R =25V
Forward operating resistance	C _T	–	–	1.2	pF	V _R =6V, f =1MHz
Reverse current	r _F	–	–	0.9	Ω	I _F =2mA, f =100MHz

Electrical characteristic curves

($T_A=25^\circ\text{C}$)

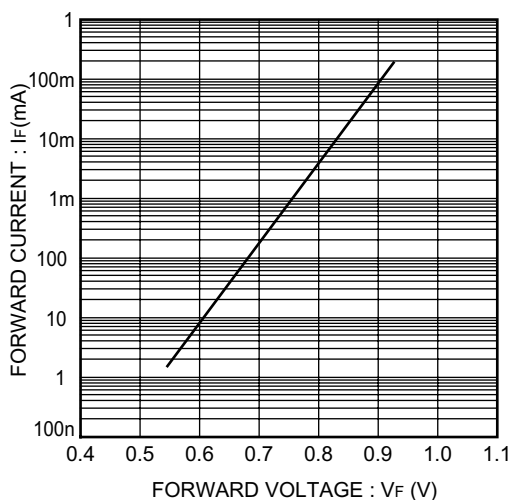


Fig. 1 Forward characteristics

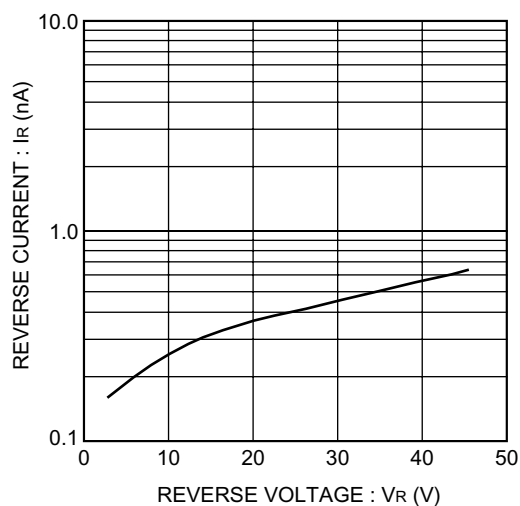


Fig. 2 Reverse characteristics

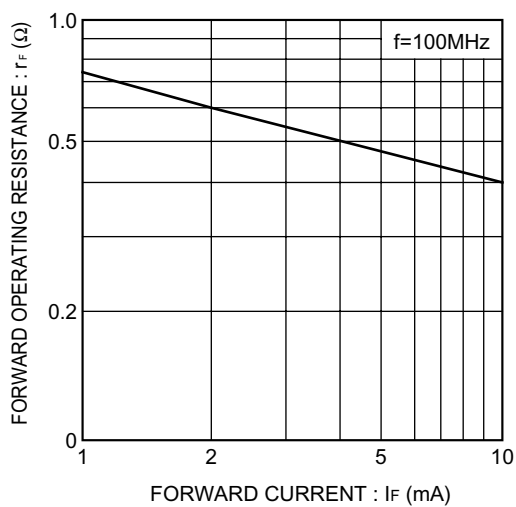


Fig. 4 Forward operating resistance characteristics

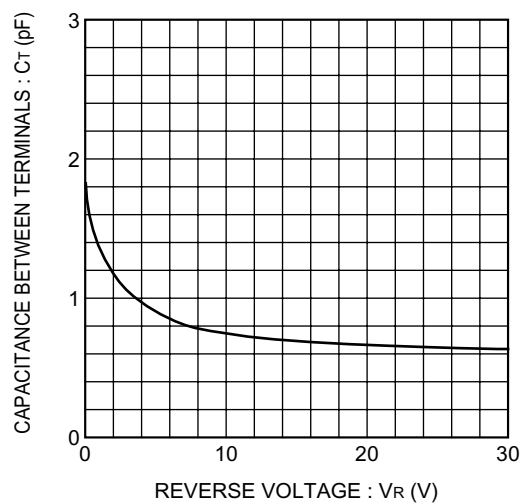
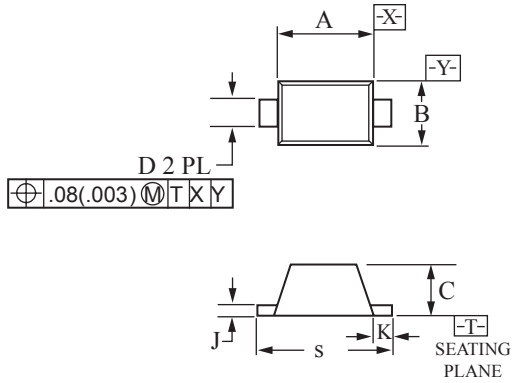


Fig. 3 Capacitance between terminals characteristics

LBA277AT1
SOD-523/SC-79

NOTES:

 1. DIMENSIONING AND TOLERANCING PER
ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETERS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.10	1.30	0.043	0.051
B	0.70	0.90	0.028	0.035
C	0.50	0.70	0.020	0.028
D	0.25	0.35	0.010	0.014
J	0.07	0.20	0.0028	0.0079
K	0.15	0.25	0.006	0.010
S	1.50	1.70	0.059	0.067